SP025N08GHTF

250V N-Channel Power MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
250V	8.0mΩ@10V	170A

合肥矽普半导体
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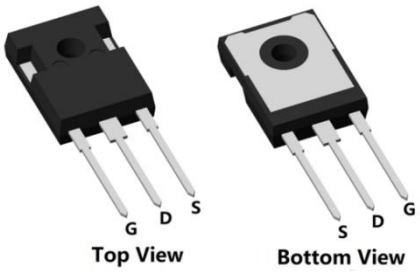
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

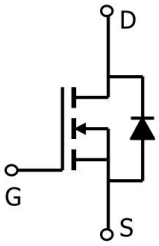
- PWM Application
- Hard switched and high frequency circuits
- Power Management

Package

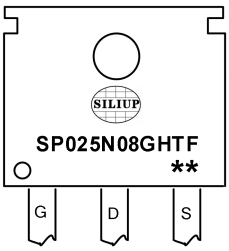


TO-247(1:G 2:D 3:S)

Circuit diagram



Marking



SP025N08GHTF : Device Code
**** : Week Code**

Order Information

Device	Package	Unit/Tube
SP025N08GHTF	TO-247	30

Absolute maximum ratings (Ta=25℃,unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	250	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current (Tc=25℃)	I_D	170	A
Continuous Drain Current (Tc=100℃)	I_D	113	A
Pulsed Drain Current	I_{DM}	680	A
Single Pulse Avalanche Energy[1]	E_{AS}	900	mJ
Power Dissipation (Tc=25℃)	P_D	540	W
Power Dissipation (Tc=100℃)	P_D	216	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.23	℃/W
Storage Temperature Range	T_{STG}	-55 to 150	℃
Operating Junction Temperature Range	T_J	-55 to 150	℃

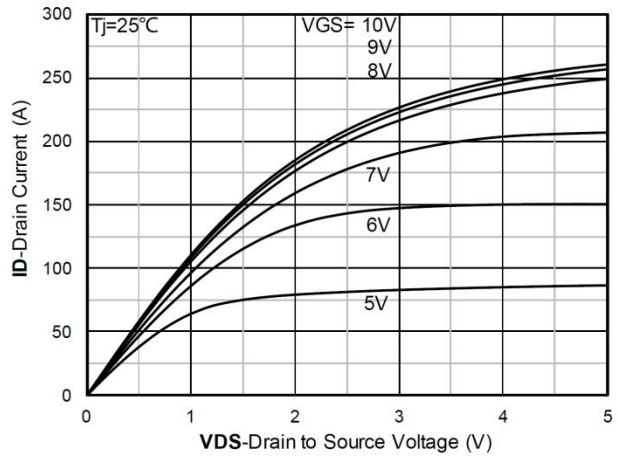
Electrical characteristics (Ta=25℃, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	VGS=0V , ID=250uA	250	-	-	V
Drain Cut-Off Current	I_{DSS}	VDS=200V , VGS=0V , TJ=25℃	-	-	1	μA
Gate Leakage Current	I_{GSS}	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	VGS=VDS , ID =250uA	2.6	3.0	3.4	V
Drain-Source ON Resistance	$R_{DS(ON)}$	VGS=10V , ID=20A	-	8.0	10.0	mΩ
Gate Resistance	R_G	VDS=125V , VGS=0V , f=1MHz	-	7	-	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	VDS=125V , VGS=0V , f=1MHz	-	8560	-	pF
Output Capacitance	C_{oss}		-	600	-	
Reverse Transfer Capacitance	C_{rss}		-	24	-	
Total Gate Charge	Q_g	VDS=125V , VGS=10V , ID=20A	-	120	-	nC
Gate-Source Charge	Q_{gs}		-	41	-	
Gate-Drain Charge	Q_{gd}		-	19	-	
Gate Pleteau Vlotage	$V_{pleteau}$		-	4.95	-	V
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	VDD=125V , VGS=10V , RG=10Ω ID=20A	-	33	-	nS
Rise Time	t_r		-	47	-	
Turn-Off Delay Time	$t_{d(off)}$		-	64	-	
Fall Time	t_f		-	34	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	I_S		-	-	170	A
Reverse Recovery Time	Trr	IS=20A, di/dt=200A/us, TJ=25℃	-	336	-	nS
Reverse Recovery Charge	Qrr		-	1590	-	nC

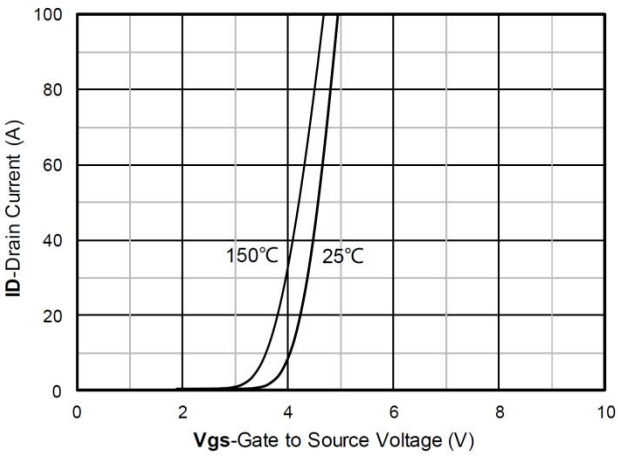
Note :

1. The test condition is VDD=50V,VGS=10V,L=0.5mH,RG=25Ω

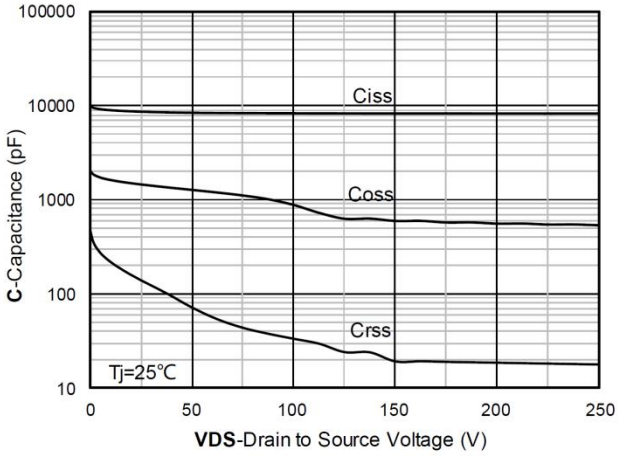
Typical Characteristics



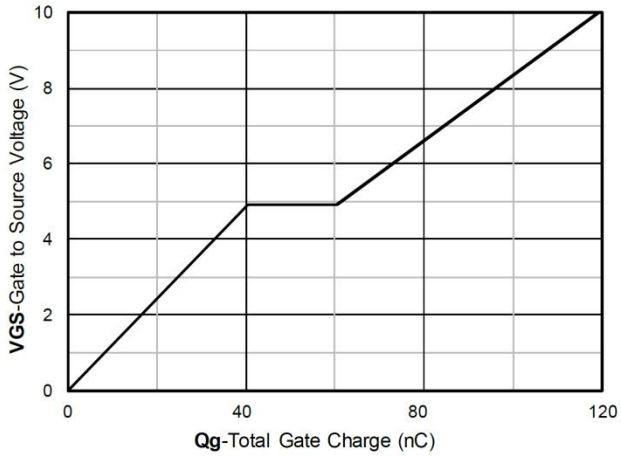
Output Characteristics



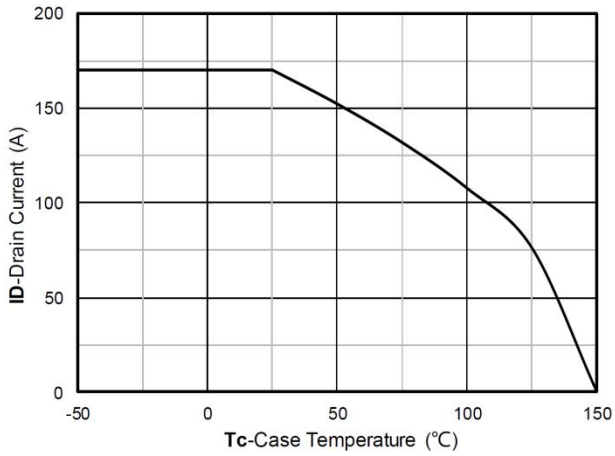
Transfer Characteristics



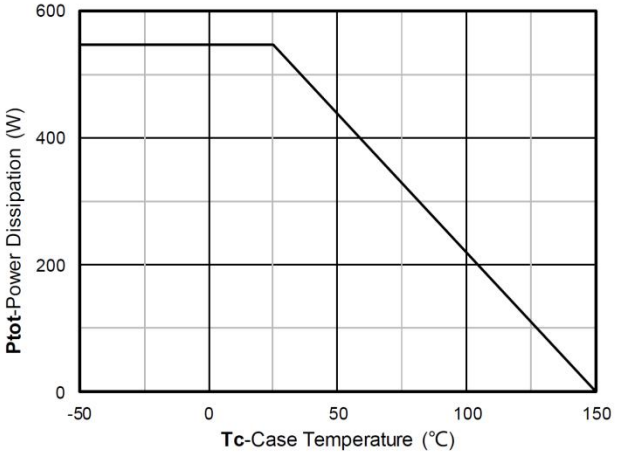
Capacitance Characteristics



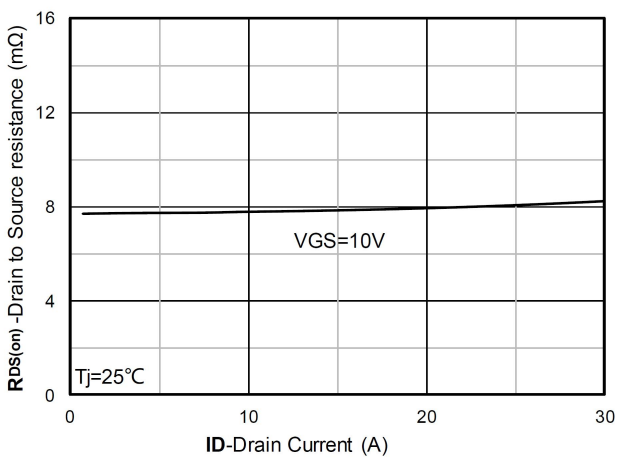
Gate Charge



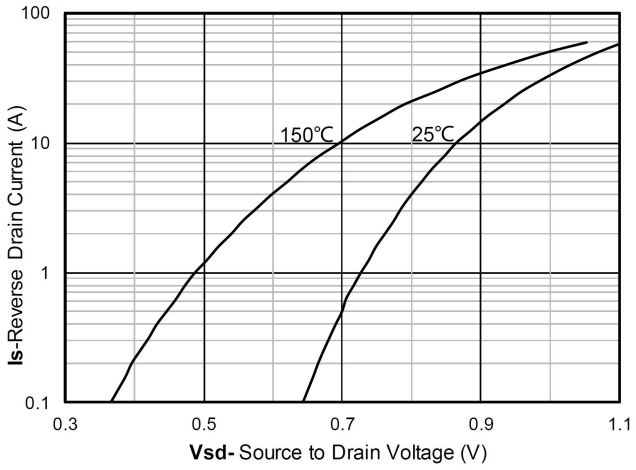
Current dissipation



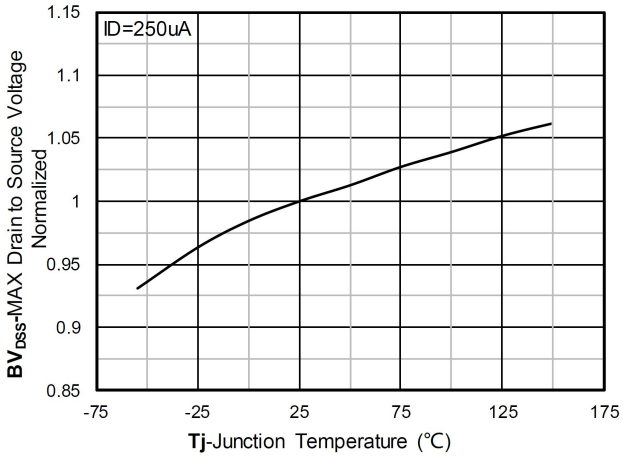
Power dissipation



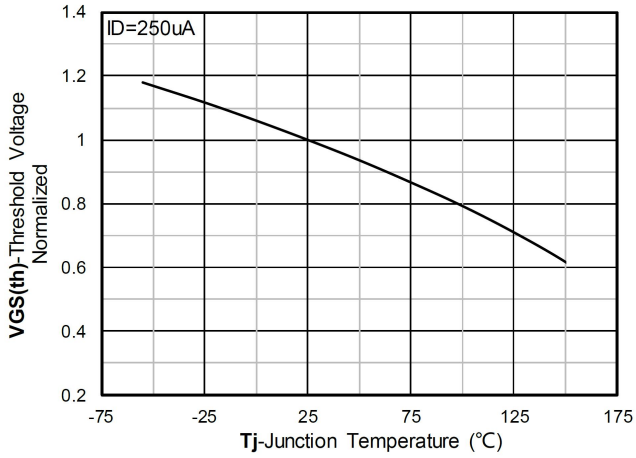
RDS(on) VS Drain Current



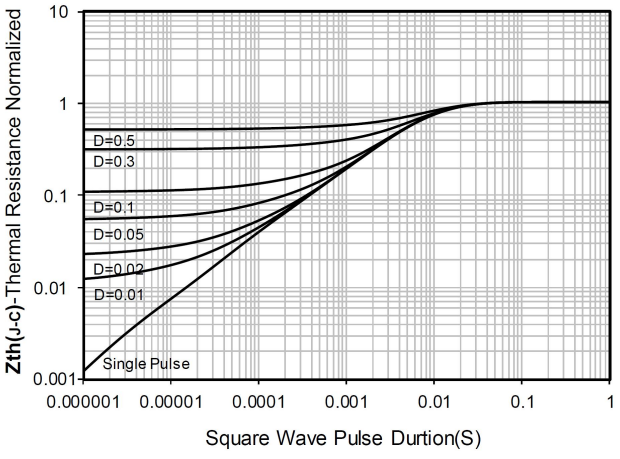
Forward characteristics of reverse diode



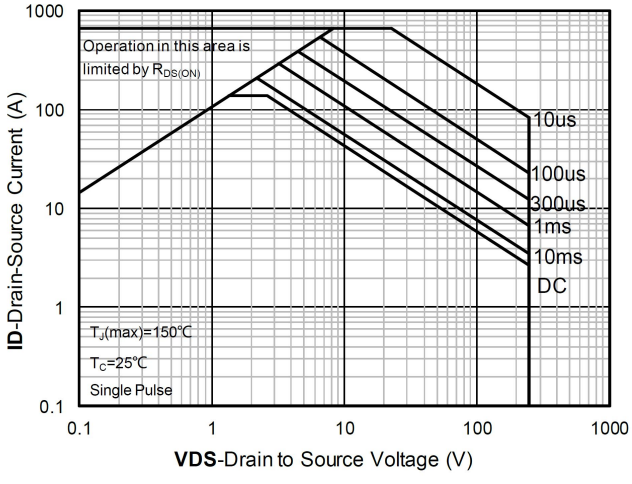
Normalized breakdown voltage



Normalized Threshold voltage



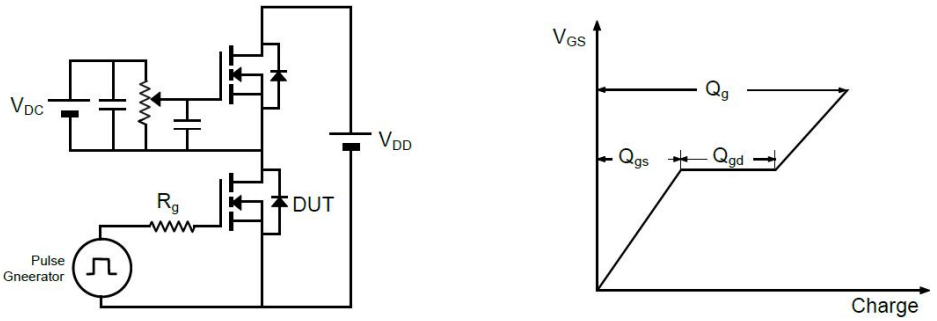
Maximum Transient Thermal Impedance



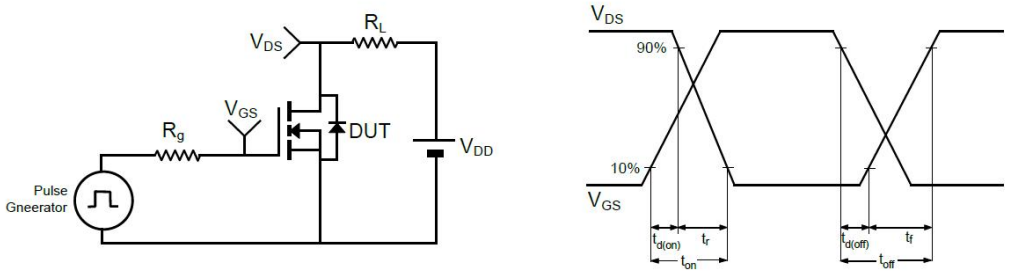
Safe Operation Area

Test Circuit

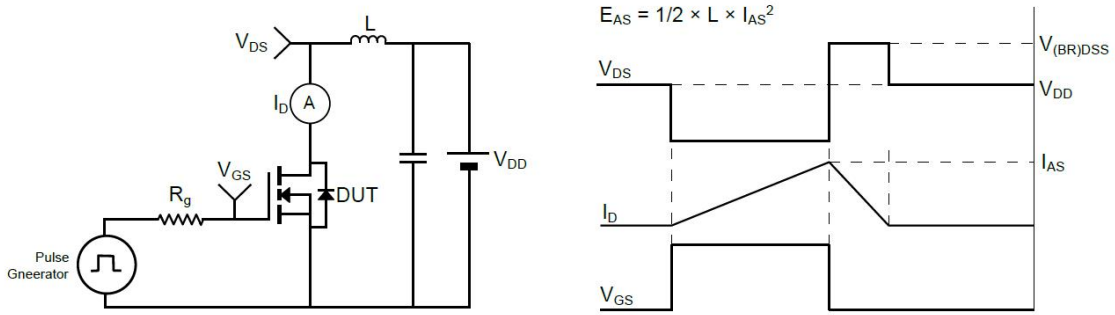
Gate Charge



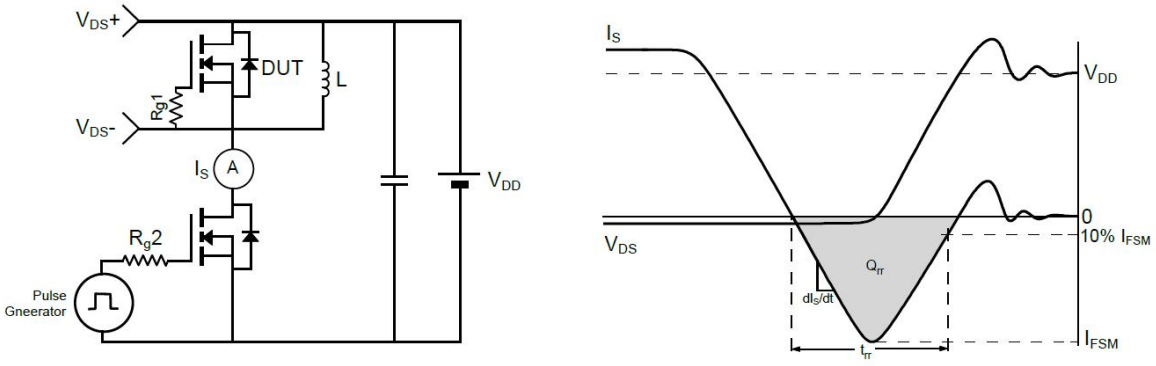
Resistive Load Switching Time



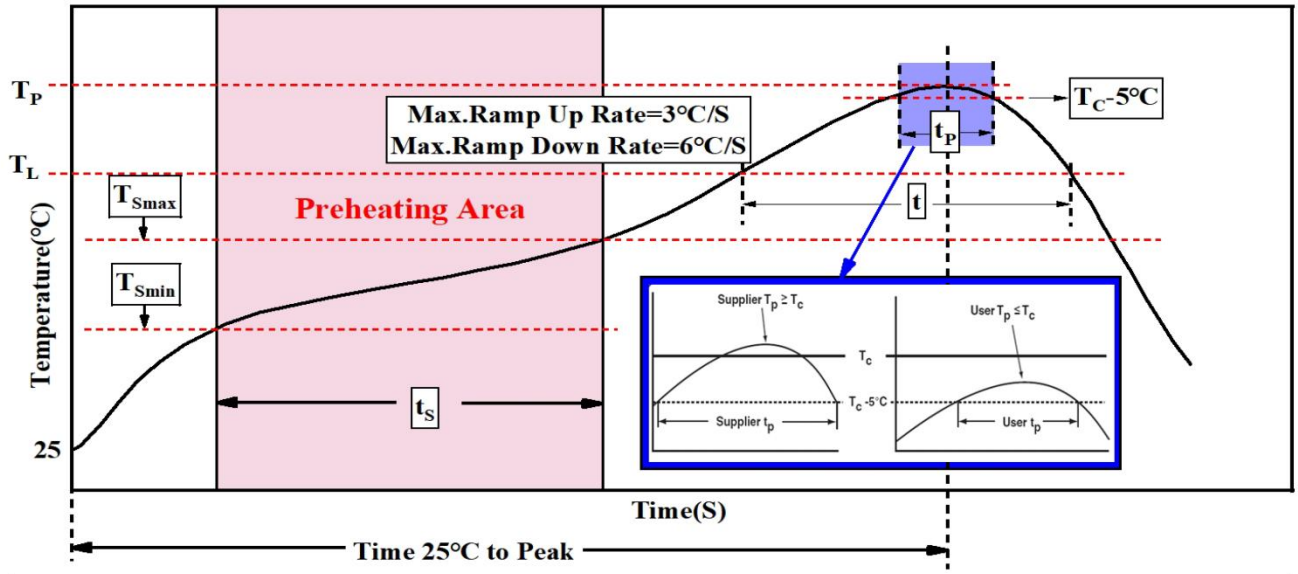
Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering(Pb-Free)



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (Tsmin) Temperature max (Tsmax) Time (Tsmin to Tsmax) (ts)	 100°C 150°C 60-120 seconds	 150°C 200°C 60-120 seconds
Average ramp-up rate (Tsmax to Tp)	3 °C/second max.	3°C/second max.
Liquidous temperature (TL) Time at liquidous (tL)	183 °C 60-150 seconds	217°C 60-150 seconds
Peak package body Temperature e (Tp)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (tp)** within 5°C of the specified classification temperature (Tc)	20** seconds	30** seconds
Average ramp-down rate (Tp to Tsmax)	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (Tp) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (tp) is defined as a supplier minimum and a user maximum		

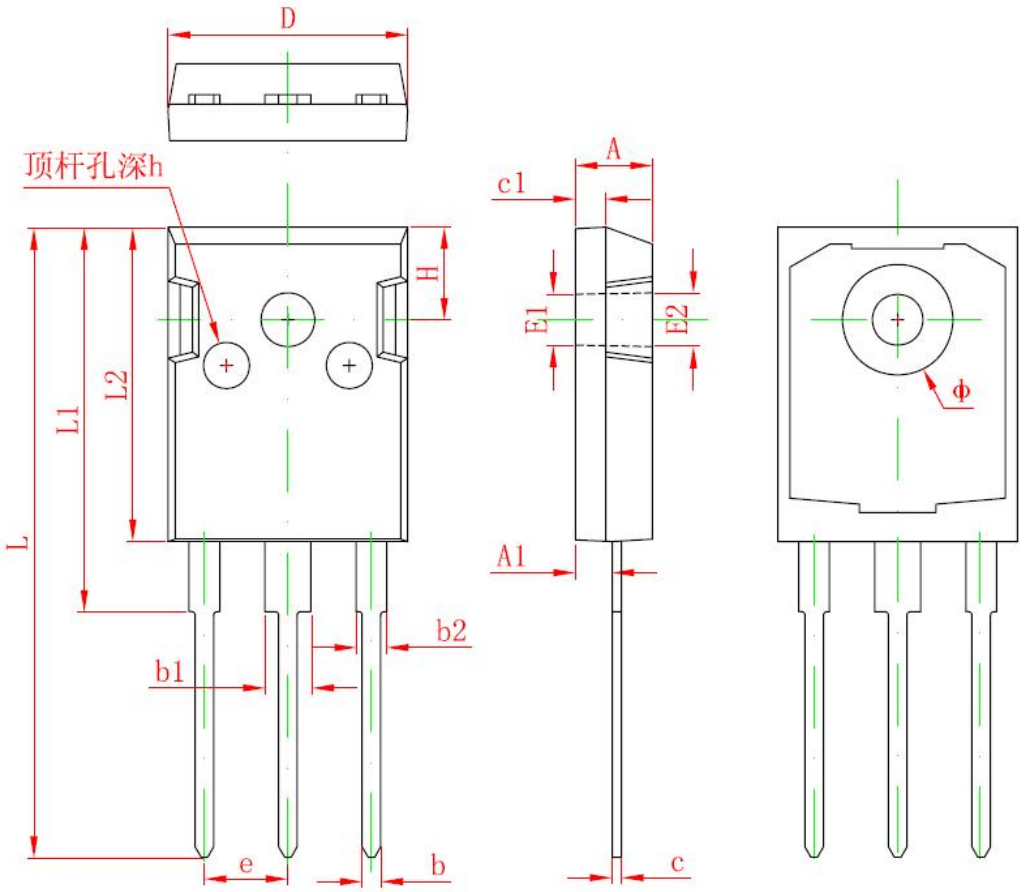
Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 350-2000	Volume mm^3 >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

TO-247 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.700	5.300
A1	2.100	2.600
b	1.000	1.400
b1	2.800	3.200
b2	1.800	2.200
c	0.500	0.700
c1	1.900	2.500
D	15.450	16.200
E1	3.500 REF.	
E2	3.600 REF.	
L	40.400	41.600
L1	24.750	25.750
L2	20.300	21.300
Φ	7.100	7.300
e	5.450 TYP.	
H	5.980 REF.	
h	0.000	0.300